

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	787	257/67-70.ccls.	US-PGPUB; USPAT	OR	OFF	2006/07/31 13:57
L5	56	L4 and ((adhe\$8 affinity bond\$6) near2 (semiconductor amorphous polycrystalline polysilicon "poly-si"))	US-PGPUB; USPAT	OR	ON	2006/07/31 13:57
L6	1596	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 with (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 14:00
L7	4	L6 and (optical adj print\$6 adj head)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 14:00
L8	1940	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) same (adhe\$8 with (semiconductor amorphous polycrystalline polysilicon)) same ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	US-PGPUB; USPAT	OR	ON	2006/07/31 15:53
L9	3	L8 and (optical adj print\$6 adj head)	US-PGPUB; USPAT	OR	ON	2006/07/31 14:03
L10	7547	257/81.ccls. 257/82.ccls. 257/84.ccls. 257/93.ccls. 257/98.ccls. 257/99.ccls. 257/693.ccls. 257/700.ccls. 257/701.ccls. 257/783.ccls.	US-PGPUB; USPAT	OR	ON	2006/07/31 14:05
L11	192	L8 and L10	US-PGPUB; USPAT	OR	ON	2006/07/31 14:05
L12	128	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) with (adhe\$8 near2 (semiconductor amorphous polycrystalline polysilicon)) with ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) near2 (semiconductor device silicon))	US-PGPUB; USPAT	OR	ON	2006/07/31 14:39

## EAST Search History

L13	134	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board) and (adhe\$8 near2 (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) near2 (semiconductor device silicon))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 15:11
L14	84	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board) same (adhe\$8 near4 (amorphous polycrystalline polysilicon)) same ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	US-PGPUB; USPAT	OR	ON	2006/07/31 15:18
L15	58	(substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board) and (adhe\$8 near4 (amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 15:26
L16	279	(optical adj print\$6 adj head)	US-PGPUB; USPAT	OR	ON	2006/07/31 15:30
L17	160	L16 same (led (light adj emit\$6))	US-PGPUB; USPAT	OR	ON	2006/07/31 15:30
L18	90	L17 same (photosensitive drum electrostatic lens)	US-PGPUB; USPAT	OR	ON	2006/07/31 15:30
L19	62	(rod adj lens adj array) and (photosensitive adj drum) and (transfer adj roller)	US-PGPUB; USPAT	OR	ON	2006/07/31 15:35
L20	1273	(optical adj print\$6 adj head)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 15:43
L21	830	L20 and (led (light adj emit\$6))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 15:43
L22	251	L21 and lens	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 15:43
L23	57	L22 and (photosensitive drum electrostatic)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/07/31 15:43

## EAST Search History

L24	19	(rod adj lens adj array) same clamp same base same hold\$6	US-PGPUB; USPAT	OR	ON	2006/07/31 15:43
L25	25	((gallium adj arsenide) gaas) same (tft (thin adj film adj transistor)) same (gate near2 (oxide dioxide insulat\$6 dielectric))	US-PGPUB; USPAT	OR	ON	2006/07/31 15:46
L26	299	257/67.ccls.	US-PGPUB; USPAT	OR	OFF	2006/07/31 15:48
L27	299	((substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 with (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))).clm.	US-PGPUB	OR	ON	2006/07/31 15:58
L28	232	((substrate wafer) and (integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 with (semiconductor amorphous polycrystalline polysilicon)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))).clm.	US-PGPUB	OR	ON	2006/07/31 15:58
L29	207	((substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 with (semiconductor amorphous polycrystalline polysilicon) with (material constituent ingredient includ\$6 compris\$6 consist\$6 bond\$6)) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))). clm.	US-PGPUB	OR	ON	2006/07/31 16:02

## EAST Search History

L30	58	((substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and (adhe\$8 with ((semiconductor amorphous polycrystalline polysilicon) near2 (material constituent ingredient includ\$6 compris\$6 consist\$6 bond\$6))) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))). clm.	US-PGPUB	OR	ON	2006/07/31 16:03
L31	170	((substrate wafer integrated semiconductor silicon pcb pwb ((circuit wiring) adj board)) and ((adhe\$8 bond\$6) with ((semiconductor amorphous polycrystalline polysilicon) near2 (material constituent ingredient includ\$6 compris\$6 consist\$6))) and ((tft (thin adj film) piezoelectric (hall adj element) (light near (emit\$6 sens\$6))) with (semiconductor device silicon))). clm.	US-PGPUB	OR	ON	2006/07/31 16:04